ESD Protection Diode Array

Quad, Low Capacitance

This integrated surge protection device is designed for applications requiring transient overvoltage protection. It is intended to be used in sensitive equipment such as wireless headsets, PDAs, digital cameras, computers, printers, communication systems, and other applications. The integrated design provides very effective and reliable protection for four separate lines using only one package. This device is ideal for situations where board space is at a premium.

Features

- ESD Protection: IEC61000-4-2: Level 4
- Four Separate Unidirectional Configurations for Protection
- Low Leakage Current < 1 μA @ 9 V
- Small SOT-953 SMT Package
- Low Capacitance
- These are Pb-Free Devices

Benefits

- Provides Protection for ESD Industry Standards: IEC 61000, HBM
- Protects Four Lines Against Transient Voltage Conditions
- Minimize Power Consumption of the System
- Minimize PCB Board Space

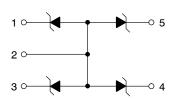
Typical Applications

- Cellular and Portable Electronics
- Serial and Parallel Ports
- Microprocessor Based Equipment
- Notebooks, Desktops, Servers



ON Semiconductor®

www.onsemi.com





SCALE 4:

SOT-953 CASE 526AE

MARKING DIAGRAM



2 = Specific Device Code

M = Date & Assembly Code

ORDERING INFORMATION

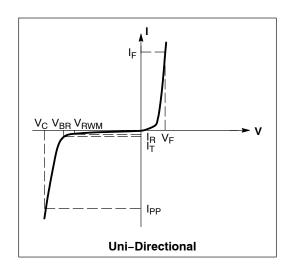
| Device | Package | Shipping [†] | | |
|--------------|----------------------|-----------------------|--|--|
| NUP412VP5T5G | SOT-953 (Pb-Free) | 8000 / Tape & Reel | | |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

| Symbol | Parameter |
|------------------|--|
| I _{PP} | Maximum Reverse Peak Pulse Current |
| V _C | Clamping Voltage @ IPP |
| V _{RWM} | Working Peak Reverse Voltage |
| I _R | Maximum Reverse Leakage Current @ V _{RWM} |
| V _{BR} | Breakdown Voltage @ I _T |
| Ι _Τ | Test Current |
| ΘV _{BR} | Maximum Temperature Coefficient of V _{BR} |
| I _F | Forward Current |
| V _F | Forward Voltage @ I _F |
| Z _{ZT} | Maximum Zener Impedance @ I _{ZT} |
| I _{ZK} | Reverse Current |
| Z _{ZK} | Maximum Zener Impedance @ I _{ZK} |



MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)

| Characteristic | Symbol | Value | Unit |
|---|---------------------------------|-------------|---------------|
| Peak Power Dissipation (8 X 20 μs @ T _A = 25°C) (Note 1) | P _{PK} | 18 | W |
| Thermal Resistance Junction-to-Ambient Above 25°C, Derate | R_{\thetaJA} | 560 4.5 | °C/W mW/°C |
| Maximum Junction Temperature | T _{Jmax} | 150 | °C |
| Operating Junction and Storage Temperature Range | T _J T _{stg} | –55 to +150 | °C |
| Lead Solder Temperature (10 seconds duration) | TL | 260 | °C |
| Human Body Model (HBM) Machine Model (MM) | ESD | 8000 400 | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS $(T_A = 25^{\circ}C)$

| | Device | V _{RP} @ 5 mA (Volts) I _{PM} @ | | • | | ge Current @ V _{RM} | Typ Capa @ 0 V B (Not | ias (pF) | Typ Capa @ 3 V B (Note | ias (pF) |
|--------------------|---------|--|-----|------|------------------|---------------------------------|-----------------------------|----------|------------------------------|----------|
| Device | Marking | Min | Nom | Max | V _{RWM} | I _{RWM} (μA) | Тур | Max | Тур | Max |
| NUP412VP5 (Note 3) | 2 | 11.4 | 12 | 12.7 | 9.0 | 0.5 | 6.5 | 10 | 3.5 | 5.0 |

Capacitance of one diode at f = 1 MHz, T_A = 25°C.
 V_{BR} at 5 mA.

^{1.} Non-repetitive current.

TYPICAL ELECTRICAL CHARACTERISTICS

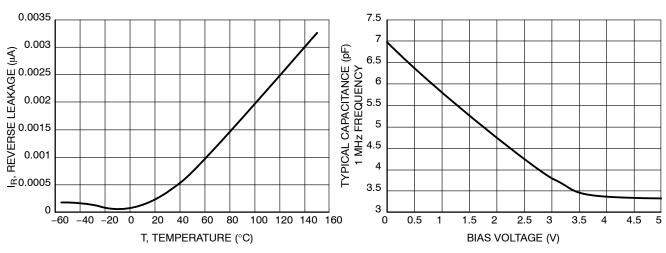


Figure 1. Reverse Leakage versus Temperature

Figure 2. Capacitance

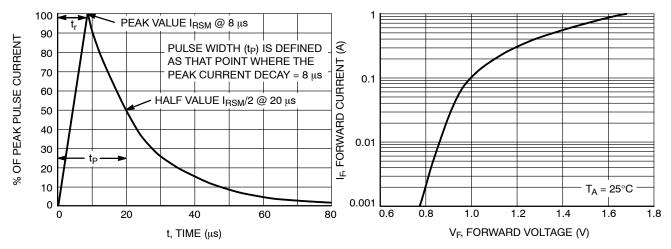


Figure 3. $8 \times 20 \mu s$ Pulse Waveform

Figure 4. Forward Voltage

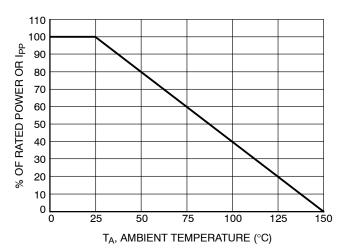
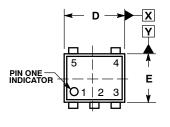


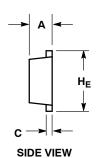
Figure 5. Power Derating Curve

PACKAGE DIMENSIONS

SOT-953 CASE 527AE ISSUE E



TOP VIEW

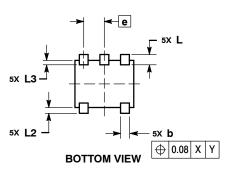


NOTES:

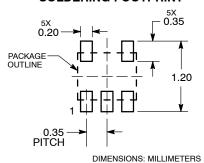
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- MINIMUM THICKNESS OF THE BASE MATERIAL.

 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| | MILLIMETERS | | | | | | |
|-----|-------------|------|------|--|--|--|--|
| DIM | MIN | NOM | MAX | | | | |
| Α | 0.34 | 0.37 | 0.40 | | | | |
| b | 0.10 | 0.15 | 0.20 | | | | |
| С | 0.07 | 0.12 | 0.17 | | | | |
| D | 0.95 | 1.00 | 1.05 | | | | |
| Е | 0.75 | 0.80 | 0.85 | | | | |
| е | 0.35 BSC | | | | | | |
| HE | 0.95 | 1.00 | 1.05 | | | | |
| L | 0.175 REF | | | | | | |
| L2 | 0.05 | 0.10 | 0.15 | | | | |
| 13 | | | 0.15 | | | | |



SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns me rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative